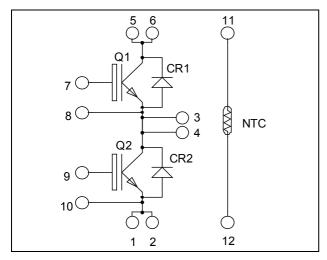
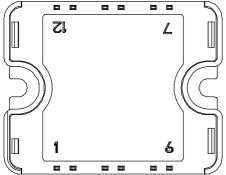


# Phase leg Fast Trench + Field Stop IGBT3 Power Module

 $V_{CES} = 1200V$  $I_{C} = 50A @ Tc = 80°C$ 





Pins 1/2; 3/4; 5/6 must be shorted together

#### Application

- Welding converters
- Switched Mode Power Supplies
- Uninterruptible Power Supplies
- Motor control

#### **Features**

- Fast Trench + Field Stop IGBT3 Technology
  - Low voltage drop
  - Low tail current
  - Switching frequency up to 20 kHz
  - Soft recovery parallel diodes
  - Low diode VF
  - Low leakage current
  - RBSOA and SCSOA rated
- Very low stray inductance
  - Symmetrical design
- Internal thermistor for temperature monitoring
- High level of integration

#### Benefits

- Outstanding performance at high frequency operation
- Direct mounting to heatsink (isolated package)
- Low junction to case thermal resistance
- Solderable terminals both for power and signal for easy PCB mounting
- Low profile
- RoHS Compliant

#### Absolute maximum ratings

Symbol	Parameter		Max ratings	Unit
$V_{CES}$	Collector - Emitter Breakdown Voltage		1200	V
ī	Continuous Collector Current	$T_C = 25^{\circ}C$	75	
$I_{C}$	Continuous Conector Current	$T_C = 80$ °C	50	Α
$I_{CM}$	Pulsed Collector Current	$T_C = 25^{\circ}C$	100	
$V_{GE}$	Gate – Emitter Voltage		±20	V
$P_{\mathrm{D}}$	Maximum Power Dissipation	$T_C = 25^{\circ}C$	277	W
RBSOA	Reverse Bias Safe Operating Area	$T_{\rm J} = 125^{\circ}{\rm C}$	100A @ 1150V	

TAUTION: These Devices are sensitive to Electrostatic Discharge. Proper Handling Procedures Should Be Followed. See application note APT0502 on www.microsemi.com



# All ratings @ $T_j = 25$ °C unless otherwise specified

## **Electrical Characteristics**

Symbol	Characteristic	Test Conditions		Min	Typ	Max	Unit
$I_{CES}$	Zero Gate Voltage Collector Current	$V_{GE} = 0V, V_{CE} = 1200V$				250	μΑ
V <sub>CE(sat)</sub>	Collector Emitter Saturation Voltage	$V_{GE} = 15V$	$T_j = 25^{\circ}C$	1.4	1.7	2.1	V
		$I_C = 50A$ $T_j = 125$ °C			2.0		V
$V_{GE(th)}$	Gate Threshold Voltage	$V_{GE} = V_{CE}$ , $I_C = 2mA$		5.0	5.8	6.5	V
$I_{GES}$	Gate – Emitter Leakage Current	$V_{GE} = 20V, V_{CE} = 0V$				400	nA

## **Dynamic Characteristics**

Symbol	Characteristic	Test Conditions		Min	Typ	Max	Unit
$C_{ies}$	Input Capacitance	$V_{GE} = 0V, V_{CE} = 25V$			3600		pF
$C_{rss}$	Reverse Transfer Capacitance	f = 1MHz	f = 1MHz				pr.
$T_{d(on)}$	Turn-on Delay Time	Inductive Switch	ning (25°C)		90		
$T_{r}$	Rise Time	$V_{GE} = \pm 15V$			30		ns
$T_{d(off)}$	Turn-off Delay Time	$V_{\text{Bus}} = 600V$ $I_{\text{C}} = 50A$			420		
$T_{\mathrm{f}}$	Fall Time	$R_G = 18\Omega$		70		Ì	
$T_{d(on)}$	Turn-on Delay Time	Inductive Switching (125°C) $V_{GE} = \pm 15V$ $V_{Bus} = 600V$ $I_{C} = 50A$ $R_{G} = 18\Omega$			90		
$T_{r}$	Rise Time				50		
$T_{d(off)}$	Turn-off Delay Time				520		ns
$T_{\mathrm{f}}$	Fall Time				90		
Eon	Turn-on Switching Energy	$V_{GE} = \pm 15V$ $V_{Bus} = 600V$	$T_j = 125$ °C		5		T
$E_{ m off}$	Turn-off Switching Energy	$I_C = 50A$ $R_G = 18\Omega$	$T_j = 125^{\circ}C$		5.5		mJ

# Reverse diode ratings and characteristics

Symbol	Characteristic	Test Conditions	Test Conditions		Typ	Max	Unit
$V_{RRM}$	Maximum Peak Repetitive Reverse Voltage			1200			V
$I_{RM}$	Maximum Reverse Leakage Current	V <sub>R</sub> =1200V	$T_j = 25^{\circ}C$			250	μA
1KM	Waximani Reverse Bearage Carrent	VR 1200 V	$T_j = 125$ °C			500	μπ
$I_{\mathrm{F}}$	DC Forward Current		$Tc = 80^{\circ}C$		50		A
$V_{\mathrm{F}}$	Diode Forward Voltage	$I_F = 50A$	$T_i = 25^{\circ}C$		1.6	2.1	V
V F	Diode Forward Voltage	IF JOA	$T_{i} = 125^{\circ}C$		1.6		
t <sub>rr</sub>	Reverse Recovery Time	$I_F = 50A$ $V_R = 600V$ $di/dt = 1900A/\mu s$	$T_j = 25^{\circ}C$		170		ns
чr	reverse recovery Time		$T_j = 125$ °C		280		113
$Q_{rr}$	Reverse Recovery Charge		$T_j = 25^{\circ}C$		5.6		μC
Q <sub>rr</sub>	Reverse Recovery Charge		$T_j = 125$ °C		9.9		μС
Е	E. I Reverse Recovery Energy		$T_j = 25^{\circ}C$		2.2		mJ
$\mathbf{L}_{\mathrm{r}}$		$T_j = 125$ °C		4.1	·	1113	



## Thermal and package characteristics

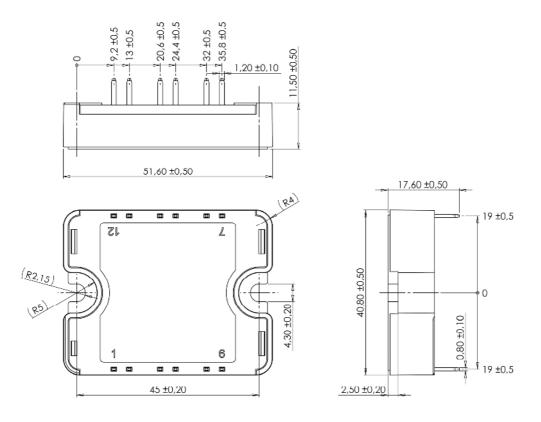
Symbol	Characteristic			Min	Тур	Max	Unit
D	Junction to Case Thermal Resistance	IGBT			0.45	°C/W	
$R_{thJC}$			Diode			0.72	C/ W
$V_{ISOL}$	RMS Isolation Voltage, any terminal to case t =1 min, 50/60Hz			4000			V
$T_{J}$	Operating junction temperature range			-40		150	
$T_{STG}$	Storage Temperature Range			-40		125	°C
$T_{\rm C}$	Operating Case Temperature					100	
Torque	Mounting torque	To heatsink	M4	2		3	N.m
Wt	Package Weight					80	g

Temperature sensor NTC (see application note APT0406 on www.microsemi.com for more information).

Symbol	Characteristic	Min	Тур	Max	Unit
R <sub>25</sub>	Resistance @ 25°C		50		kΩ
B <sub>25/85</sub>	$T_{25} = 298.15 \text{ K}$		3952		K

$$R_{T} = \frac{R_{25}}{\exp \left[ B_{25/85} \left( \frac{1}{T_{25}} - \frac{1}{T} \right) \right]} \quad \text{T: Thermistor temperature } \\ R_{T}: \text{ Thermistor value at T}$$

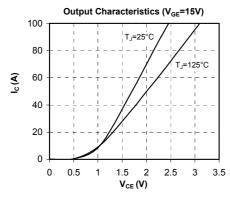
# SP1 Package outline (dimensions in mm)

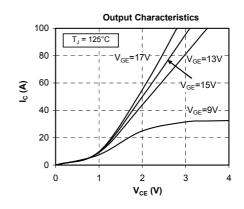


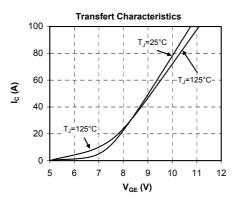
See application note 1904 - Mounting Instructions for SP1 Power Modules on www.microsemi.com

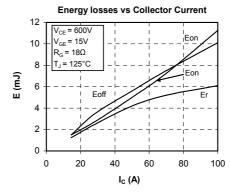


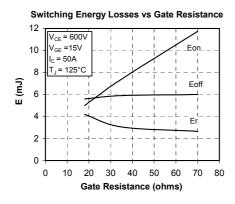
## **Typical Performance Curve**

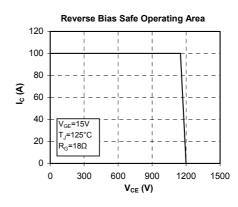


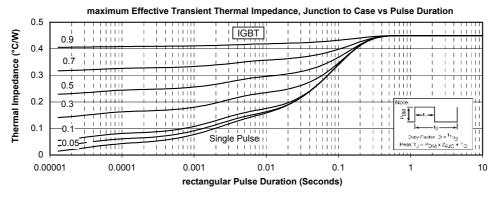




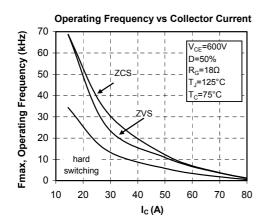


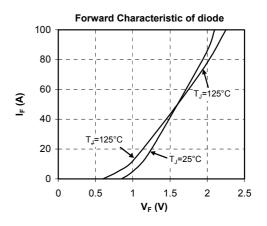


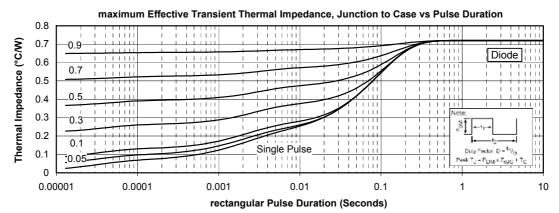












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